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Author Correction: Laser slice thinning of GaN-on-GaN high electron mobility transistors

Atsushi Tanaka, Ryuji Sugiura, Daisuke Kawaguchi, Yotaro Wani, Hirotaka Watanabe, Hadi Sena, Yuto Ando, Yoshio Honda, Yasunori Igasaki, Akio Wakejima, Yuji Ando & Hiroshi Amano

Correction to: *Scientific Reports* <https://doi.org/10.1038/s41598-022-10610-4>, published online 05 May 2022.

The original version of this Article contained a repeated error where the symbol for micrometres “ μm ” was incorrectly given as millimetres “mm” in the Introduction, Experiments, Results and discussion, Figure 2 legend and the Conclusion. This error has been corrected throughout the text.

The original Article has been corrected.



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